

# BAV99WT1, BAV99RWT1

Preferred Devices

## Dual Series Switching Diodes

The BAV99WT1 is a smaller package, equivalent to the BAV99LT1.

### Features

- Pb-Free Packages are Available

### Suggested Applications

- ESD Protection
- Polarity Reversal Protection
- Data Line Protection
- Inductive Load Protection
- Steering Logic

### MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	70	Vdc
Forward Current	$I_F$	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	$V_{RRM}$	70	V
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-Repetitive Peak Forward Current $t = 1.0 \mu s$ $t = 1.0 ms$ $t = 1.0 S$	$I_{FSM}$	2.0 1.0 0.5	A

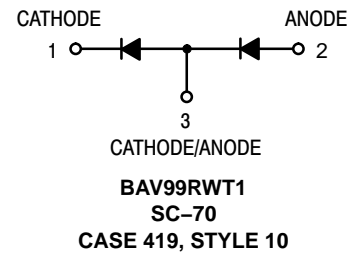
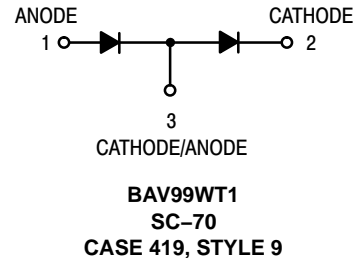
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

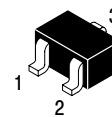


ON Semiconductor®

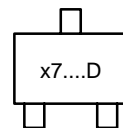
<http://onsemi.com>



### MARKING DIAGRAM



**SC-70**  
**CASE 419**



A7 = BAV99WT1  
F7 = BAV99RWT1  
D = Date Code

### ORDERING INFORMATION

Device	Package	Shipping†
BAV99WT1	SC-70	3000/Tape & Reel
BAV99WT1G	SC-70 (Pb-Free)	3000/Tape & Reel
BAV99RWT1	SC-70	3000/Tape & Reel
BAV99RWT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

# BAV99WT1, BAV99RWT1

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	200 1.6	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

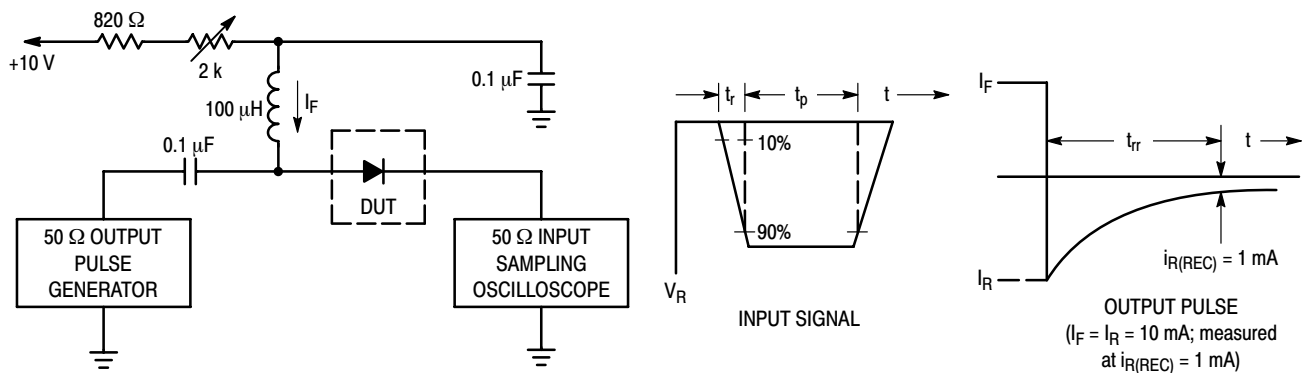
## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

### OFF CHARACTERISTICS

Reverse Breakdown Voltage ( $I_{BR} = 100 \mu\text{A}$ )	$V_{(BR)}$	70	-	Vdc
Reverse Voltage Leakage Current ( $V_R = 70 \text{ Vdc}$ ) ( $V_R = 25 \text{ Vdc}, T_J = 150^\circ\text{C}$ ) ( $V_R = 70 \text{ Vdc}, T_J = 150^\circ\text{C}$ )	$I_R$	- - -	2.5 30 50	$\mu\text{Adc}$
Diode Capacitance ( $V_R = 0, f = 1.0 \text{ MHz}$ )	$C_D$	-	1.5	pF
Forward Voltage ( $I_F = 1.0 \text{ mAdc}$ ) ( $I_F = 10 \text{ mAdc}$ ) ( $I_F = 50 \text{ mAdc}$ ) ( $I_F = 150 \text{ mAdc}$ )	$V_F$	- - - -	715 855 1000 1250	mVdc
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mAdc}, i_{R(REC)} = 1.0 \text{ mAdc}$ ) (Figure 1) $R_L = 100 \Omega$	$t_{rr}$	-	6.0	ns
Forward Recovery Voltage ( $I_F = 10 \text{ mA}, t_r = 20 \text{ ns}$ )	$V_{FR}$	-	1.75	V

- FR-5 =  $1.0 \times 0.75 \times 0.062 \text{ in.}$
- Alumina =  $0.4 \times 0.3 \times 0.024 \text{ in.}$  99.5% alumina.



- Notes: (a) A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of 10 mA.  
 (b) Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10 mA.  
 (c)  $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

# BAV99WT1, BAV99RWT1

## CURVES APPLICABLE TO EACH DIODE

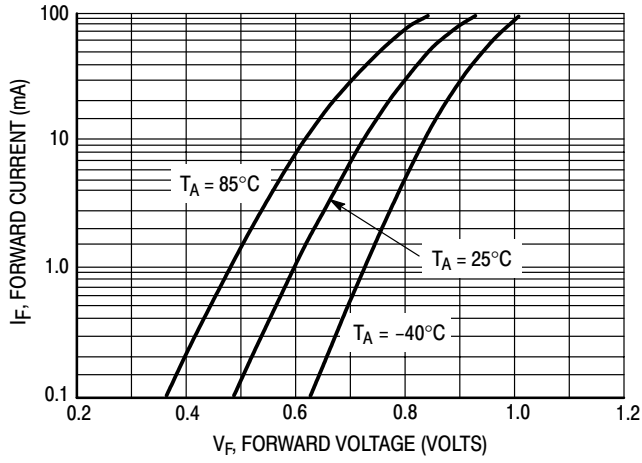


Figure 2. Forward Voltage

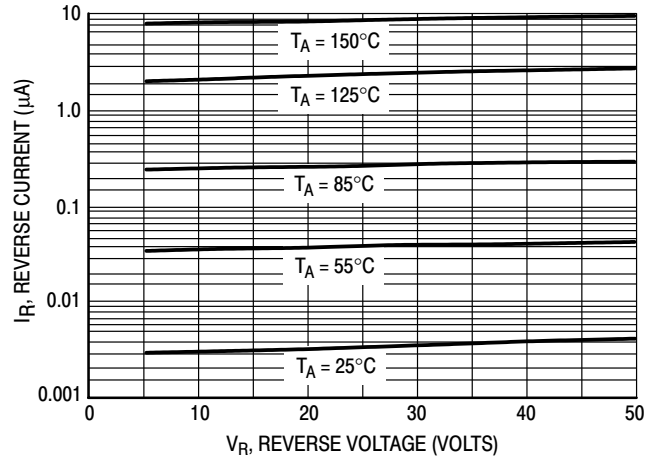


Figure 3. Leakage Current

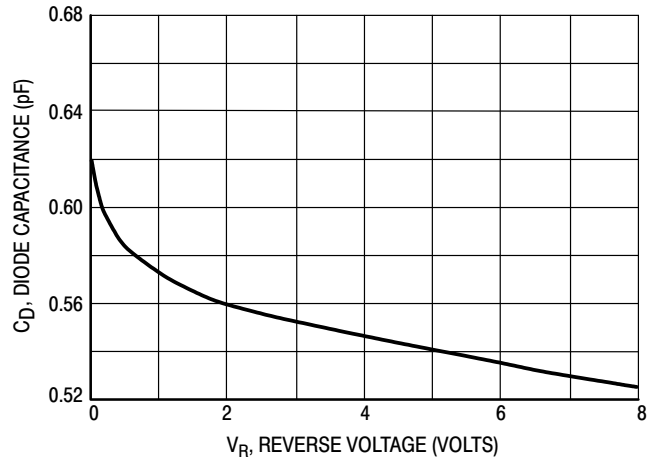
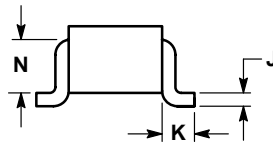
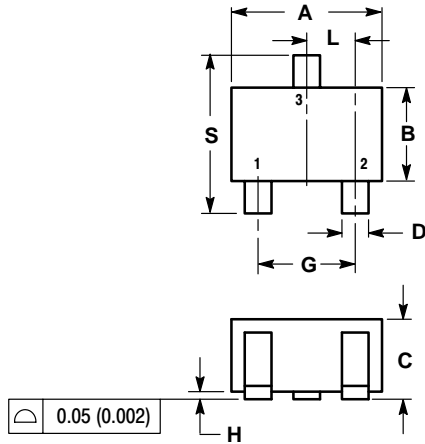


Figure 4. Capacitance

# BAV99WT1, BAV99RWT1

## PACKAGE DIMENSIONS

SC-70 (SOT-323)  
CASE 419-04  
ISSUE L



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

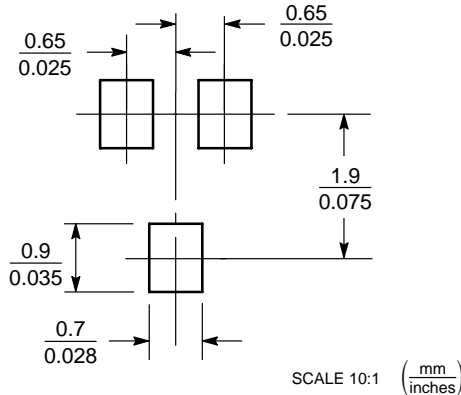
STYLE 9:

- PIN 1. ANODE
- CATHODE
- CATHODE-ANODE

STYLE 10:

- PIN 1. CATHODE
- ANODE
- ANODE-CATHODE

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
P.O. Box 61312, Phoenix, Arizona 85082-1312 USA

Phone: 480-829-7710 or 800-344-3860 Toll Free USA/Canada  
Fax: 480-829-7709 or 800-344-3867 Toll Free USA/Canada  
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free  
USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center  
2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051  
Phone: 81-3-5773-3850

ON Semiconductor Website: <http://onsemi.com>

Order Literature: <http://www.onsemi.com/litorder>

For additional information, please contact your local Sales Representative.